

## N-Channel 40 V (D-S) MOSFET

PRODUCT SUMMARY			
V <sub>DS</sub> (V)	R <sub>DS(on)</sub> (mΩ)(Typ.)	I <sub>D</sub> (A) <sup>a</sup>	Q <sub>g</sub> (Typ.)
40	2.7 at V <sub>GS</sub> = 10 V	100	120 nC
	3.2 at V <sub>GS</sub> = 4.5 V	70	

### FEATURES

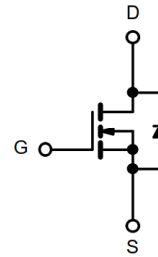
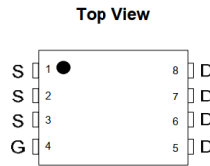
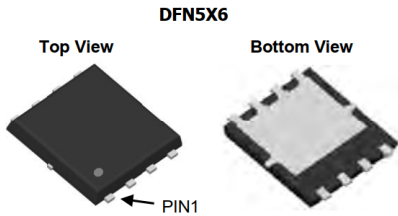
- DT-Trench Power MOSFET
- 100 % R<sub>g</sub> and UIS tested



RoHS  
COMPLIANT

### APPLICATIONS

- Notebook PC Core
- VRM/POL



N-Channel MOSFET

### ABSOLUTE MAXIMUM RATINGS (T<sub>A</sub> = 25 °C, unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V <sub>DS</sub>	40	V
Gate-Source Voltage	V <sub>GS</sub>	± 20	
Continuous Drain Current (T <sub>J</sub> = 175 °C)	I <sub>D</sub>	T <sub>C</sub> = 25 °C	100 <sup>a</sup>
		T <sub>C</sub> = 70 °C	88
		T <sub>A</sub> = 25 °C	25 <sup>b, c</sup>
		T <sub>A</sub> = 70 °C	20 <sup>b, c</sup>
Pulsed Drain Current	I <sub>DM</sub>	300	A
Avalanche Current Pulse	I <sub>AS</sub>	22	
Single Pulse Avalanche Energy		E <sub>AS</sub>	
Continuous Source-Drain Diode Current	I <sub>S</sub>	T <sub>C</sub> = 25 °C	100 <sup>a</sup>
		T <sub>A</sub> = 25 °C	3.06 <sup>b, c</sup>
Maximum Power Dissipation	P <sub>D</sub>	T <sub>C</sub> = 25 °C	250 <sup>a</sup>
		T <sub>C</sub> = 70 °C	175
		T <sub>A</sub> = 25 °C	3.45 <sup>b, c</sup>
		T <sub>A</sub> = 70 °C	2.41 <sup>b, c</sup>
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	- 55 to 175	°C

### THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient <sup>b, d</sup>	R <sub>thJA</sub>	35	43.5	°C/W
Maximum Junction-to-Case	R <sub>thJC</sub>	0.4	0.6	

Notes:

- Based on T<sub>C</sub> = 25 °C.
- Surface mounted on 1" x 1" FR4 board.
- t = 10 s.
- Maximum under steady state conditions is 90 °C/W.

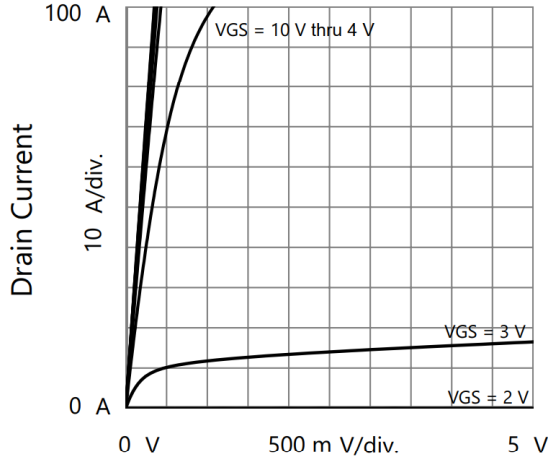
<b>SPECIFICATIONS</b> ( $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	40			V
$V_{DS}$ Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = 250\text{ }\mu\text{A}$		35		mV/°C
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$			- 5.5		
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	1		2.5	V
Gate-Source Leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 40\text{ V}, V_{GS} = 0\text{ V}$			1	$\mu\text{A}$
		$V_{DS} = 40\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$			10	
On-State Drain Current <sup>a</sup>	$I_{D(on)}$	$V_{DS} \geq 5\text{ V}, V_{GS} = 10\text{ V}$	100			A
Drain-Source On-State Resistance <sup>a</sup>	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 30\text{ A}$		2.7	3.5	$\Omega$
		$V_{GS} = 4.5\text{ V}, I_D = 30\text{ A}$		3.2	4.0	
Forward Transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = 15\text{ V}, I_D = 30\text{ A}$		110		S
<b>Dynamic<sup>b</sup></b>						
Input Capacitance	$C_{iss}$	$V_{DS} = 20\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$		6480		$\mu\text{F}$
Output Capacitance	$C_{oss}$			469		
Reverse Transfer Capacitance	$C_{rss}$			445		
Total Gate Charge	$Q_g$	$V_{DS} = 20\text{ V}, V_{GS} = 10\text{ V}, I_D = 30\text{ A}$		120		nC
Gate-Source Charge	$Q_{gs}$			12.5		
Gate-Drain Charge	$Q_{gd}$			20		
Gate Resistance	$R_g$	$f = 1\text{ MHz}$		1.1		$\Omega$
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 20\text{ V}, R_L = 0.555\text{ }\Omega$ $I_D \cong 30\text{ A}, V_{GEN} = 10\text{ V}, R_g = 1\text{ }\Omega$		18		ns
Rise Time	$t_r$			12		
Turn-Off Delay Time	$t_{d(off)}$			70		
Fall Time	$t_f$			10		
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 20\text{ V}, R_L = 0.625\text{ }\Omega$ $I_D \cong 30\text{ A}, V_{GEN} = 4.5\text{ V}, R_g = 1\text{ }\Omega$		58		
Rise Time	$t_r$			185		
Turn-Off Delay Time	$t_{d(off)}$			59		
Fall Time	$t_f$			14		
<b>Drain-Source Body Diode Characteristics</b>						
Continuous Source-Drain Diode Current	$I_S$	$T_C = 25\text{ }^\circ\text{C}$			100	A
Pulse Diode Forward Current <sup>a</sup>	$I_{SM}$				300	
Body Diode Voltage	$V_{SD}$	$I_S = 1\text{ A}$		0.6	1.2	V
Body Diode Reverse Recovery Time	$t_{rr}$	$I_F = 30\text{ A}, di/dt = 100\text{ A}/\mu\text{s}, T_J = 25\text{ }^\circ\text{C}$		55	78	ns
Body Diode Reverse Recovery Charge	$Q_{rr}$			123.2		nC
Reverse Recovery Fall Time	$t_a$			30		ns
Reverse Recovery Rise Time	$t_b$			29		

**Notes:**

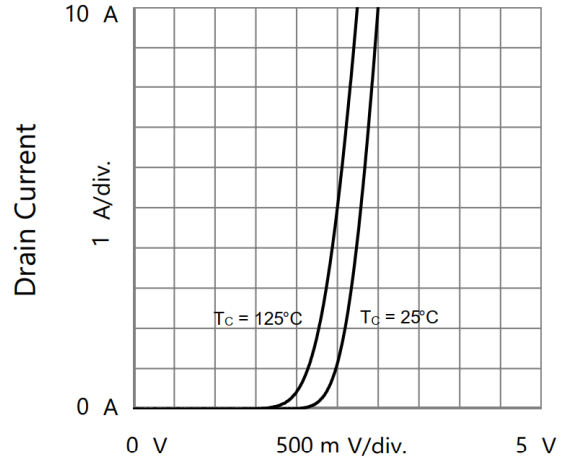
- a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .  
 b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

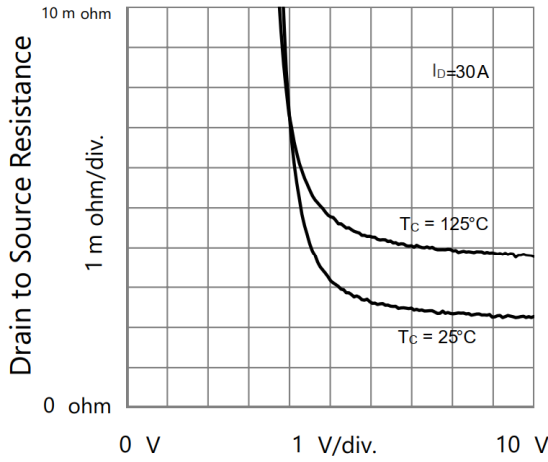
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



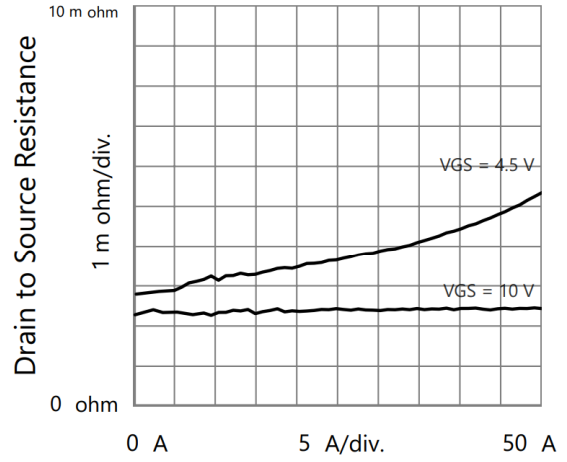
Drain to Source Voltage  
Output Characteristics



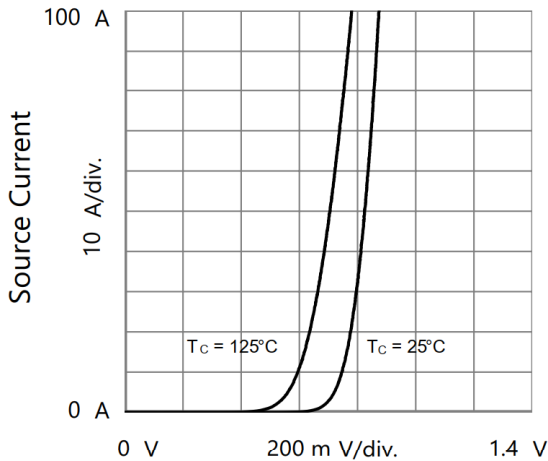
Gate to Source Voltage  
Transfer Characteristics



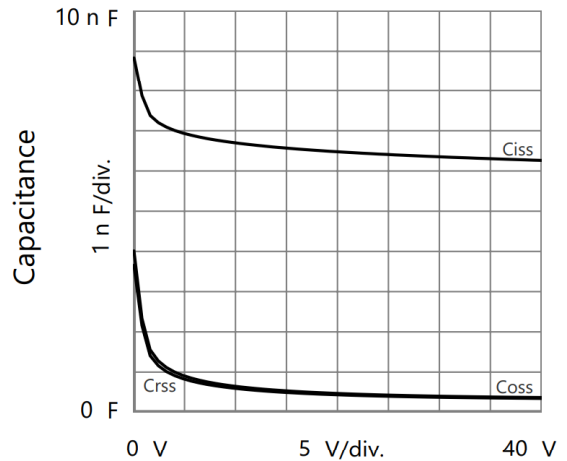
Gate to Source Voltage  
Drain to Source Resistance vs. Gate to Source Voltage



Drain Current  
Drain to Source Resistance vs. Drain Current

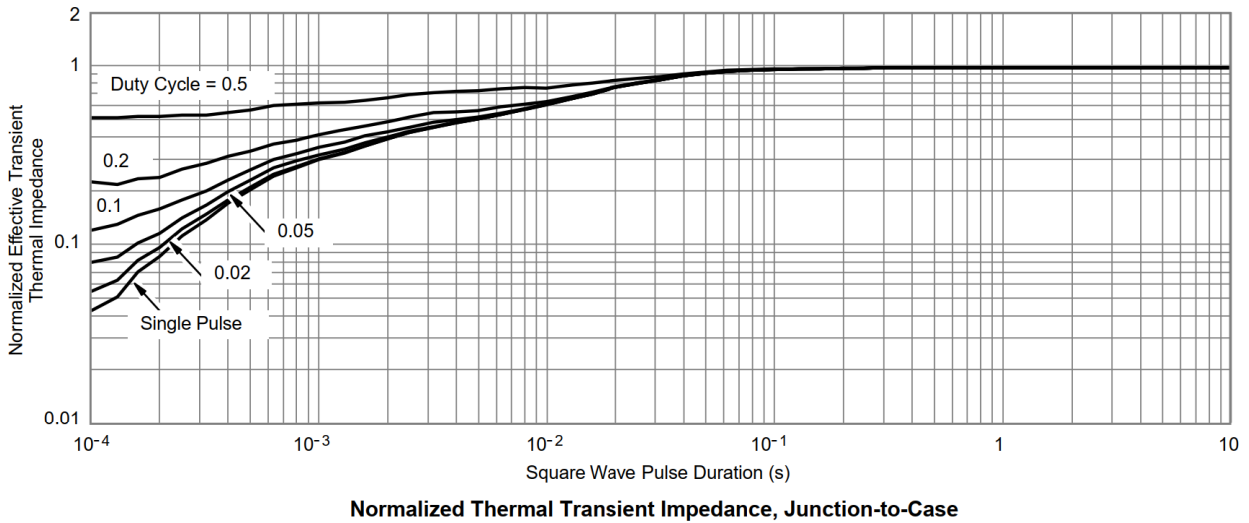
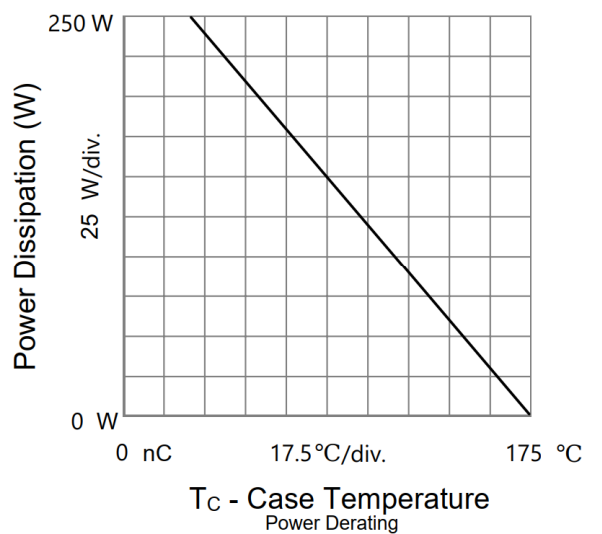
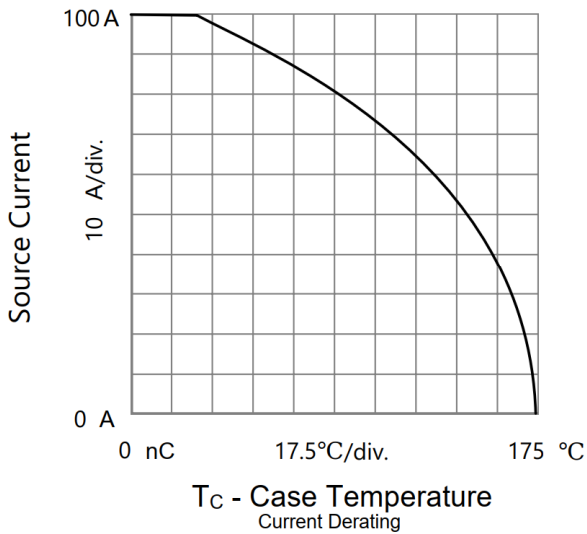
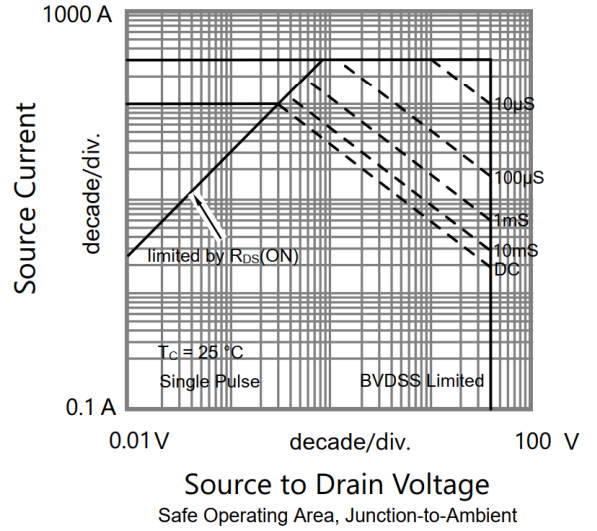
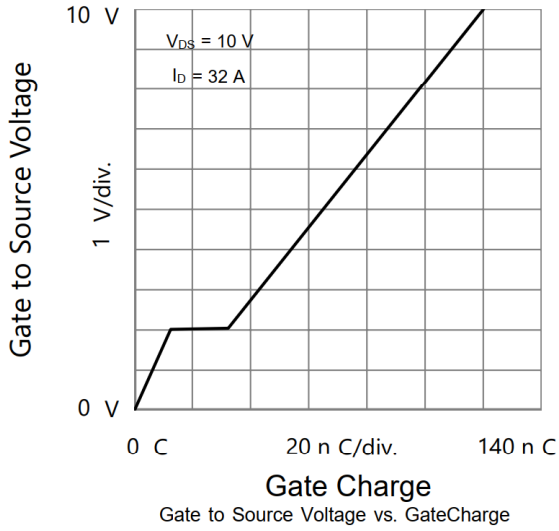


Source to Drain Voltage  
Body Diode Forward Characteristics

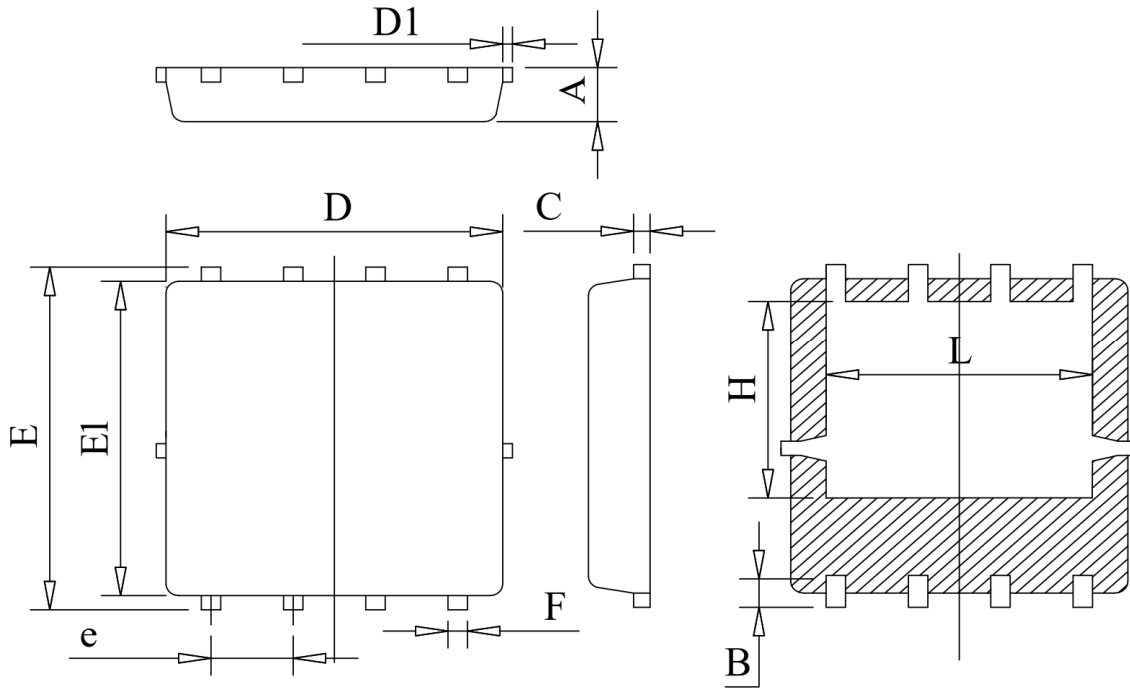


Drain to Source Voltage  
Capacitances

**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



DFN5X6-8L PACKAGE OUTLINE



COMMON DIMENSIONS  
(UNITS OF MEASURE=MILLIMETER)

Unit : mm

Symbol	Min	Typ	Max
A	0.78	0.95	1.12
B	0.45	0.58	0.78
C	0.18	0.254	0.36
D	4.70	5.20	5.45
D1			0.18
E	5.85	6.05	6.25
E1	5.38	5.55	5.98
e	1.15	1.27	1.40
F	0.18	0.30	0.52
H	3.25	3.47	3.70
L	3.75	4.00	4.25

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